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**The impact of surface states on the DC and RF characteristics of AlGa<sub>N</sub>/Ga<sub>N</sub> HFETs**

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687	Inverse temperature dependence of reverse gate leakage current in AlGa <sub>N</sub> /Ga <sub>N</sub> HEMT. <b>2013</b> , 28, 015026		15
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681	Influences of gate drive on pulsed current collapse recovery in AlGa <sub>N</sub> /Ga <sub>N</sub> power HEMTs. <b>2013</b> ,		
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446	Study of different algorithms and models for trapping effect extraction. <b>2016</b> ,		
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421	Identification of Energy and Spatial Location of Electron Traps in AlGaN/GaN HFET Structures. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 1642-1646	2.9	2
420	. <b>2017</b> , 38, 937-940		21
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414	Comparison of Two DC Extraction Methods for Mobility and Parasitic Resistances in a HEMT. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 1528-1534	2.9	4
413	Anomalous DC and RF behavior of virgin AlGaN/AlN/GaN HEMTs. <b>2017</b> , 32, 035011		6
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401	. <b>2017</b> ,		2
400	Comparison for $1/f$ Noise Characteristics of AlGa <sub>x</sub> N/GaN FinFET and Planar MISHFET. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 3634-3638	2.9	20
399	Neutral beam process in AlGa <sub>x</sub> N/GaN HEMTs: Impact on current collapse. <b>2017</b> , 137, 1-5		6
398	Positive Shift in Threshold Voltage Induced by CuO and NiO <sub>x</sub> Gate in AlGa <sub>x</sub> N/GaN HEMTs. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 3139-3144	2.9	14
397	Physics-Based Multi-Bias RF Large-Signal GaN HEMT Modeling and Parameter Extraction Flow. <b>2017</b> , 5, 310-319		30
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394	Thickness engineering of atomic layer deposited Al <sub>2</sub> O <sub>3</sub> films to suppress interfacial reaction and diffusion of Ni/Au gate metal in AlGa <sub>x</sub> N/GaN HEMTs up to 600 °C in air. <b>2017</b> , 110, 253505		7
393	Effect of Barrier Thickness on Linearity of Underlap AlInN/GaN DG-MOSHEMTs. <b>2017</b> , 12, 1750009		2
392	Performance enhancement of AlGa <sub>x</sub> N/GaN nanochannel omega-FinFET. <b>2017</b> , 129, 196-199		4
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389	Substrates and Materials. <b>2017</b> , 27-52		
388	Self-heating and polarization effects in AlGa <sub>x</sub> N/AlN/GaN/AlGa <sub>x</sub> N based devices. <b>2017</b> ,		1
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384	Buffer trapping effects on knee walkout in GaN HEMTs. <b>2017</b> ,			
383	Robust Performance of AlGa <sub>N</sub> -Channel Metal-Insulator-Semiconductor High-Electron-Mobility Transistors at High Temperatures. <b>2017</b> , 34, 128501			
382	High-resistivity unintentionally carbon-doped GaN layers with nitrogen as nucleation layer carrier gas grown by metal-organic chemical vapor deposition. <b>2017</b> , 7, 125018			4
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380	Thermodynamic photoinduced disorder in AlGa <sub>N</sub> nanowires. <b>2017</b> , 7, 125113			10
379	Bias- and temperature-assisted trapping/de-trapping of ron degradation in D-mode AlGa <sub>N</sub> /Ga <sub>N</sub> MIS-HEMTs on a Si substrate. <b>2017</b> ,			0
378	Impact of Substrate Bias Polarity on Buffer-Related Current Collapse in AlGa <sub>N</sub> /Ga <sub>N</sub> -on-Si Power Devices. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 5048-5056	2.9		42
377	DC and RF characterzationof field plated AlGa <sub>N</sub> /Ga <sub>N</sub> HEMT. <b>2017</b> ,			1
376	An investigation on current collapse induced memory effects of GaN power amplifier for LTE base station applications. <b>2017</b> ,			
375	High breakdown (958 V) low threshold GaN HEMT. <b>2017</b> ,			1
374	Development of HEMT device with surface passivation for a low leakage current and steep subthreshold slope. <b>2017</b> ,			1
373	Current linearity and operation stability in Al <sub>2</sub> O <sub>3</sub> -gate AlGa <sub>N</sub> /Ga <sub>N</sub> MOS high electron mobility transistors. <b>2017</b> , 56, 101001			41
372	Current Collapse-Free and Self-Heating Performances in Normally Off GaN Nanowire GAA-MOSFETs. <b>2018</b> , 6, 354-359			4
371	Effect of Hydrogen on Defects of AlGa <sub>N</sub> /Ga <sub>N</sub> HEMTs Characterized by Low-Frequency Noise. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 1321-1326	2.9		26
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